

ABSTRACT

Disclosed is a plating-pretreatment solution comprising an organic sulfonic acid, thiourea, fluoroboric acid and hypophosphorous acid. Also

5 disclosed is a plating-pretreatment method comprising contacting a film carrier tape in which a wiring pattern is formed on a surface of an insulating film with a plating-pretreatment solution comprising an organic sulfonic acid, thiourea, fluoroboric acid and

10 hypophosphorous acid to remove metals remaining on the insulating film. According to the plating-pretreatment solution and the plating-pretreatment method, metals remaining on the surface of the insulating film exposed by etching can be removed, and occurrence of migration

15 can be prevented.